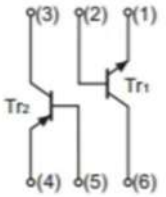
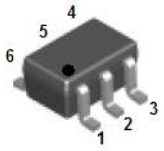
LST2515PN

Low Vce(sat) Transistors(NPN+PNP)

Features

- Transistor elements are independent, eliminating Interference.
- Mounting cost and area can be cut in half.
- Low VCE(sat).
- Non-Halogen.





SOT-363

Mechanical Data

- Case: SOT-363

Maximum Ratings (@T_A=25℃ unless otherwise specified)

Symbol	Parameter	Value	Units
Per transistor			
V_{CBO}	Collector-Base Voltage	15	V
V_{CEO}	Collector-Emitter Voltage	15	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current - Continuous	500	mA
Thermal Characteristic			
P_{tot}	Total Power Dissipation, $T_a \leqslant 25℃$	200	mW
T_J	Junction Temperature	150	℃
T_j, T_{stg}	Junction and Storage Temperature	-55 to +150	℃
$R_{th\ (j\text{-}a)}$	Thermal resistance from junction to ambient	625	℃/W

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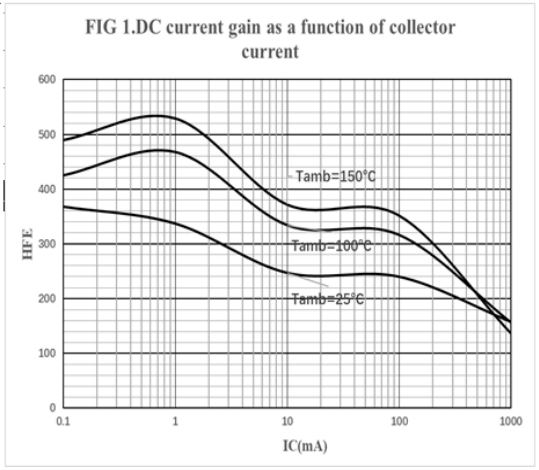
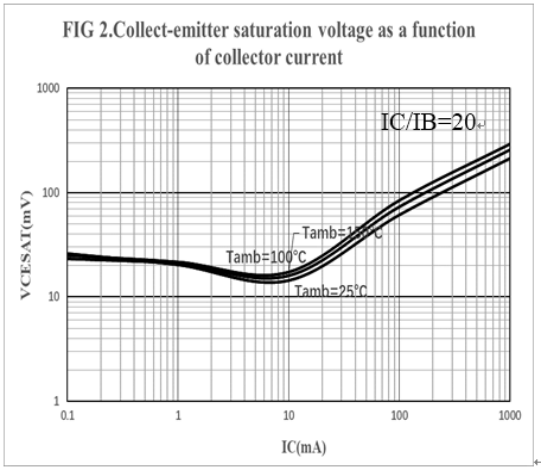
Electrical Characteristics (@T_A=25℃ unless otherwise specified)

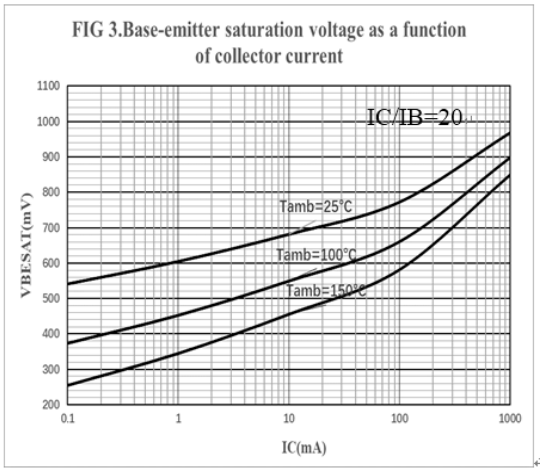
Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	I_C = 10uA, I_E = 0	15	-	-	V
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	I_C = 1mA, I_B = 0	15	-	-	V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	I_E = 10uA, I_C = 0	6	-	-	V
RCollector Cut-Off Current	I_{CBO}	V_{CB} = 15V, I_E = 0	-	-	0.1	uA
Emitter Cut-Off Current	I_{EBO}	V_{EB} =5V, I_C = 0	-	-	0.1	uA
DC Current Gain	h_{FE}	V_{CE} = 2V, I_C = 10mA	200	-	-	
Output Capacitance		V_{CE} = 2V, I_C = 100mA	150	-	-	
Reverse Transfer Capacitance		V_{CE} = 2V, I_C = 500mA	90	-	-	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	I_C= 10mA, I_B=0.5mA	-	-	25	mV
		I_C= 200mA, I_B=10mA	-	-	150	
		I_C= 500mA, I_B=50mA	-	-	250	
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	I_C= 500mA, I_B=50mA	-	-	1.1	V
Transition Frequency	f_T	V_{CE} = 6V, I_C = 20mA, f = 30MHz	150	-	-	MHz
Collector Output Capacitance	C_{ob}	V_{CB} = 10V, I_E = 0, f = 1MHz	-	-	10	pF

Ratings and Characteristic Curves (TA=25℃ unless otherwise noted)

TR1 (NPN):







TR2 (PNP):

FIG 4.DC current gain as a function of collector current

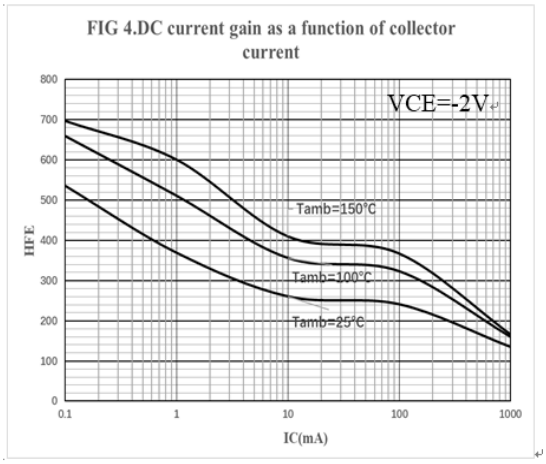


FIG 5.Collect-emitter saturation voltage as a function of collector current

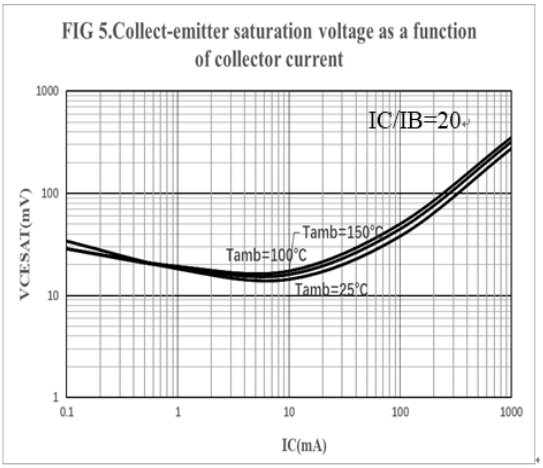
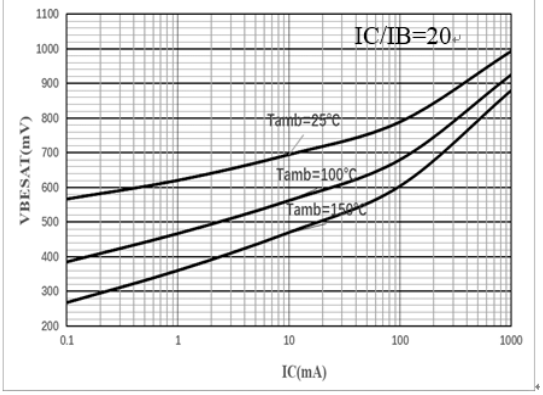


FIG 6.Base-emitter saturation voltage as a function of collector current



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Package Outline Dimensions(unit:mm)

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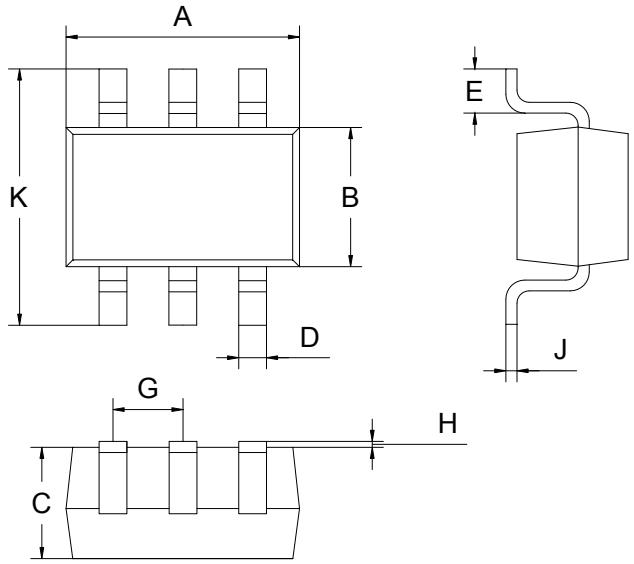

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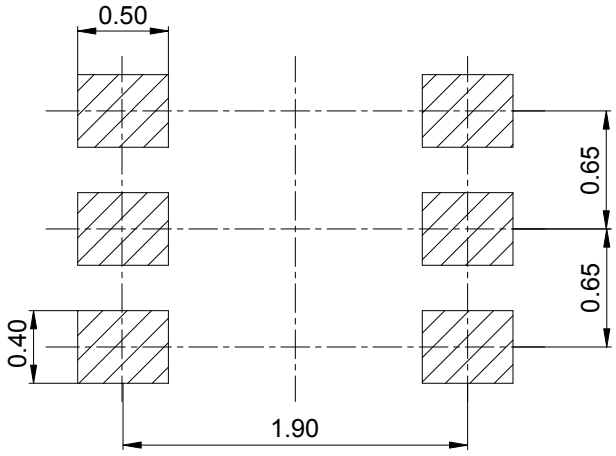
Dim	Min	Max
A	2.00	2.20
B	1.15	1.35
C	0.85	1.05
D	0.15	0.35
E	0.25	0.40
G	0.60	0.70
H	0.02	0.10
J	0.05	0.15
K	2.20	2.40

SOLDERING FOOTPRINT(unit:mm)



Ordering Information

Part Number	Package	Shipping	Marking Code
LST2515PN	SOT-363	3000/Tape&Reel	2515